PATENT S/N Unknown

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Kie Y. Ahn et al.

Examiner:

Unknown

Serial No.:

Unknown

Group Art Unit:

Unknown

Filed:

Herewith

Docket:

303.686US3

Title:

MULTILEVEL COPPER INTERCONNECTS WITH LOW-K DIELECTRICS AND AIR

GAPS

INFORMATION DISCLOSURE STATEMENT

MS Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 et. seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 10/093244, filed on March 06, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date of Deposit: February 25, 2004

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O.Box 1450, Alexandria, VA 22313-1450.

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Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE Unknown **Application Number** STATEMENT BY APPLICANT Even Date Herewith Filing Date (Use as many sheets as necessary) Ahn, Kie **First Named Inventor Group Art Unit** Unknown **Examiner Name** Unknown Attorney Docket No: 303.686US3 Sheet 1 of 13

		US PA	ATENT DOCUMENT	S		
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	US20020014646	02/07/2002	Tsu, , et al.	257	296	
	US20020028552	03/07/2002	Lee, , et al.	438	243	
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(Use as many sheets as necessary)	Filing Date	Even Date Herewith		
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	Group Art Unit	Unknown		
	Examiner Name	Unknown		
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Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE **Application Number** Unknown STATEMENT BY APPLICANT **Filing Date** Even Date Herewith (Use as many sheets as necessary) Ahn, Kie **First Named Inventor Group Art Unit** Unknown Unknown **Examiner Name** Attorney Docket No: 303.686US3 Sheet 13 of 13

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